



PTO/SB/08A (10-01)

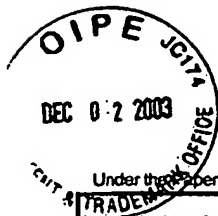
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	10/614,160
				Filing Date	July 8, 2003
				First Named Inventor	John T. Moore, et al.
				Art Unit	4848 2827
				Examiner Name	Not Yet Assigned V. Nguyen
				Attorney Docket Number	M4065.0715/P715
Sheet	1	of	11		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.†	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code² (if known)			
W	AA	2002/0000666	1/3/2002	Kozicki et al.	
W	AB	2002/0072188	6/13/2002	Gilton	
W	AC	2002/0106849	08/08/2002	Moore	
	AH	2002/0123169	09/05/2002	Moore et al.	
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W	AT1	2003/0210564	11/13/2003	Kozicki et al.	

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				Art Unit	4810 2827 2827
				Examiner Name	Not Yet Assigned V. N. Nguyen
Sheet	2	of	11	Attorney Docket Number	M4065.0715/P715

UN	AU1	3,622,319	11/1971	Sharp	
UN	AV1	3,743,847	7/1973	Boland	
	AW1	4,269,935	5/1981	Masters et al.	
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				Art Unit	4818 2827
				Examiner Name	Not Yet Assigned V. Nguyen
Sheet	3	of	11	Attorney Docket Number	M4065.0715/P715

W	AR3	6,329,606	12/2001	Freyman et al.	
W	AS3	6,348,365	2/19/2002	Moore et al.	
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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ^o
		Country Code ² -Number ³ -Kind Code ⁴ (if known)				
W	BA	56126916	10/19981	Akira et al.		
W	BB	WO 97/48032	12/18/1997	Kozicki et al.		
W	BC	WO 99/28914	06/10/1999	Kozicki et al.		
W	BD	WO 00/48196	08/17/2000	Kozicki et al.		
W	BE	WO 02/21542	03/14/2002	Kozicki et al.		

Examiner Signature	V. Nguyen	Date Considered	3/31/05
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.
¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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		Application Number	10/614,160
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Filing Date	July 8, 2003
		First Named Inventor	John T. Moore, et al.
		Group Art Unit	4810-2827
		Examiner Name	Not Yet Assigned V. Nguyen
		Attorney Docket Number	M4065.0715/P715
Sheet	4	of	11

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
W	CA	Abdel-Ali, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, Vacuum 59 (2000) 845-853.	
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	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.	
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			Examiner Name	Not Yet Assigned V. Nguyen	
Sheet	5	of	11	Attorney Docket Number	M4065.0715/P715

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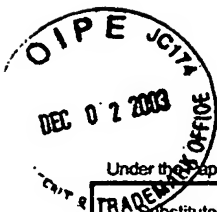
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